

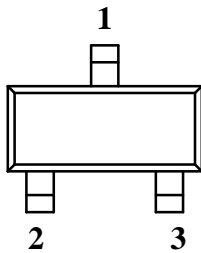
## Silicon NPN Planar RF Transistor

### Applications

RF-amplifier up to GHz range specially for wide band antenna amplifier.

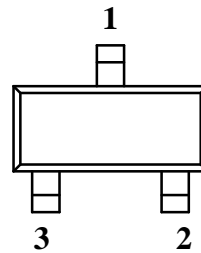
### Features

- High power gain
- Low noise figure
- High transition frequency



94 9280

BFR93 Marking: R1  
Plastic case (SOT 23)  
1= Collector; 2= Base; 3= Emitter



95 10527

BFR93R Marking: R4  
Plastic case (SOT 23)  
1= Collector; 2= Base; 3= Emitter

### Absolute Maximum Ratings

Parameters	Symbol	Value	Unit
Collector-base voltage	$V_{CBO}$	20	V
Collector-emitter voltage	$V_{CEO}$	12	V
Emitter-base voltage	$V_{EBO}$	2	V
Collector current	$I_C$	40	mA
Total power dissipation $T_{amb} \leq 60^\circ\text{C}$	$P_{tot}$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-65 to +150	$^\circ\text{C}$

### Maximum Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient	$R_{thJA}$	450	K/W

## Electrical DC Characteristics

$T_j = 25^\circ\text{C}$ , unless otherwise specified

Parameters / Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Collector-emitter cut-off current $V_{CE} = 20\text{ V}, V_{BE} = 0$	$I_{CES}$			100	$\mu\text{A}$
Collector-base cut-off current $V_{CB} = 10\text{ V}, I_E = 0$	$I_{CBO}$			100	nA
Emitter-base cut-off current $V_{EB} = 2\text{ V}, I_C = 0$	$I_{EBO}$			10	$\mu\text{A}$
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12			V
DC forward current transfer ratio $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}$	$h_{FE}$	25	50	150	

## Electrical AC Characteristics

$T_{amb} = 25^\circ\text{C}$

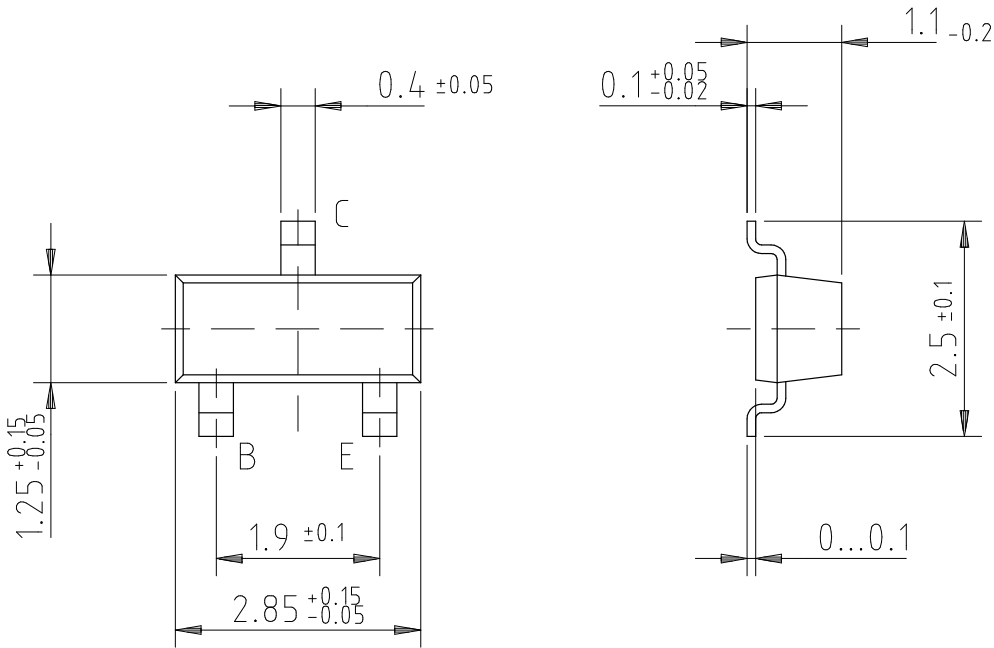
Parameters / Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Transition frequency $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}, f = 500\text{ MHz}$	$f_T$		5		GHz
Collector-emitter capacitance $V_{CE} = 5\text{ V}, f = 1\text{ MHz}$	$C_{ce}$		0.15		pF
Collector base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	$C_{cb}$		0.5		pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	$C_{eb}$		1.1		pF
Noise figure $V_{CE} = 5\text{ V}, I_C = 4\text{ mA}, Z_S = 50\ \Omega, f = 500\text{ MHz}$	F		1.9		dB
Power gain $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}, Z_L = Z_{Lopt},$ $f = 500\text{ MHz}$ $f = 800\text{ MHz}$	$G_{pe}$ $G_{pe}$		18 13		dB dB
Linear output voltage – two tone intermodulation test $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}, d_{IM} = 60\text{ dB},$ $f_1 = 806\text{ MHz}, f_2 = 810\text{ MHz}, Z_S = Z_L = 50\ \Omega$	$V_1 = V_2$		240		mV
Third order intercept point $V_{CE} = 5\text{ V}, I_C = 30\text{ mA}, f = 800\text{ MHz}$	$IP_3$		30		dBm

## Common Emitter S-Parameters

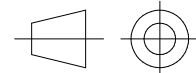
$Z_0 = 50 \Omega$

$V_{CE}/V$	$I_C/mA$	f/MHz	$S_{11}$		$S_{21}$		$S_{12}$		$S_{22}$	
			LIN MAG	ANG	LIN MAG	ANG	LIN MAG	ANG	LIN MAG	ANG
				deg		deg		deg		deg
5	5	100	0.731	-41.1	12.40	148.2	0.031	70.1	0.891	-17.4
		300	0.474	-98.0	7.54	112.4	0.061	55.9	0.618	-28.8
		500	0.358	-132.7	5.00	95.7	0.078	55.9	0.504	-27.6
		800	0.301	-166.0	3.30	81.1	0.104	59.6	0.458	-24.5
		1000	0.293	179.5	2.71	73.8	0.123	61.2	0.460	-25.5
		1200	0.299	167.4	2.33	67.0	0.143	61.8	0.457	-28.5
		1500	0.328	152.7	1.93	57.7	0.173	62.0	0.442	-34.0
		1800	0.360	138.0	1.67	49.8	0.204	61.5	0.430	-38.4
		2000	0.381	130.1	1.54	45.1	0.227	60.6	0.427	-42.5
	10	100	0.572	-56.5	18.26	137.6	0.026	68.0	0.796	-23.6
		300	0.344	-117.2	9.02	103.8	0.051	62.0	0.499	-29.7
		500	0.286	-151.4	5.72	90.4	0.073	64.7	0.413	-25.5
		800	0.259	178.7	3.69	78.1	0.106	66.7	0.392	-21.2
		1000	0.258	167.3	3.02	71.6	0.130	66.8	0.400	-22.2
		1200	0.265	157.5	2.58	65.5	0.152	66.0	0.400	-25.6
		1500	0.296	146.7	2.13	57.0	0.186	64.3	0.387	-31.3
		1800	0.327	133.7	1.84	49.5	0.220	62.3	0.374	-35.9
		2000	0.350	126.2	1.70	44.8	0.243	60.5	0.371	-40.1
	20	100	0.423	-73.5	22.83	127.4	0.022	67.3	0.688	-28.0
		300	0.272	-134.6	9.73	98.0	0.047	68.3	0.422	-28.1
		500	0.250	-165.9	6.04	86.8	0.072	70.5	0.361	-22.3
		800	0.245	168.7	3.88	75.9	0.109	70.4	0.356	-17.9
		1000	0.241	158.9	3.15	69.8	0.134	69.3	0.368	-19.5
		1200	0.252	152.0	2.69	63.9	0.158	67.7	0.369	-23.5
		1500	0.286	143.2	2.22	55.8	0.193	65.0	0.355	-29.6
		1800	0.317	130.9	1.90	48.5	0.228	62.4	0.343	-34.1
		2000	0.342	123.6	1.75	44.0	0.252	60.2	0.340	-38.5
	30	100	0.357	-84.4	24.36	122.1	0.021	68.1	0.629	-29.4
		300	0.254	-144.3	9.78	95.5	0.046	71.2	0.393	-26.0
		500	0.248	-171.9	6.04	85.2	0.072	72.6	0.346	-20.0
		800	0.245	164.9	3.86	74.7	0.110	71.5	0.347	-16.1
		1000	0.247	156.3	3.14	68.7	0.136	70.1	0.360	-18.2
		1200	0.255	150.3	2.67	63.0	0.160	68.2	0.362	-22.5
		1500	0.292	141.9	2.20	55.1	0.195	65.5	0.347	-28.6
		1800	0.325	130.3	1.89	47.9	0.230	62.5	0.337	-33.5
		2000	0.349	123.6	1.74	43.1	0.254	60.3	0.333	-38.0

## Dimensions of BFR93 in mm

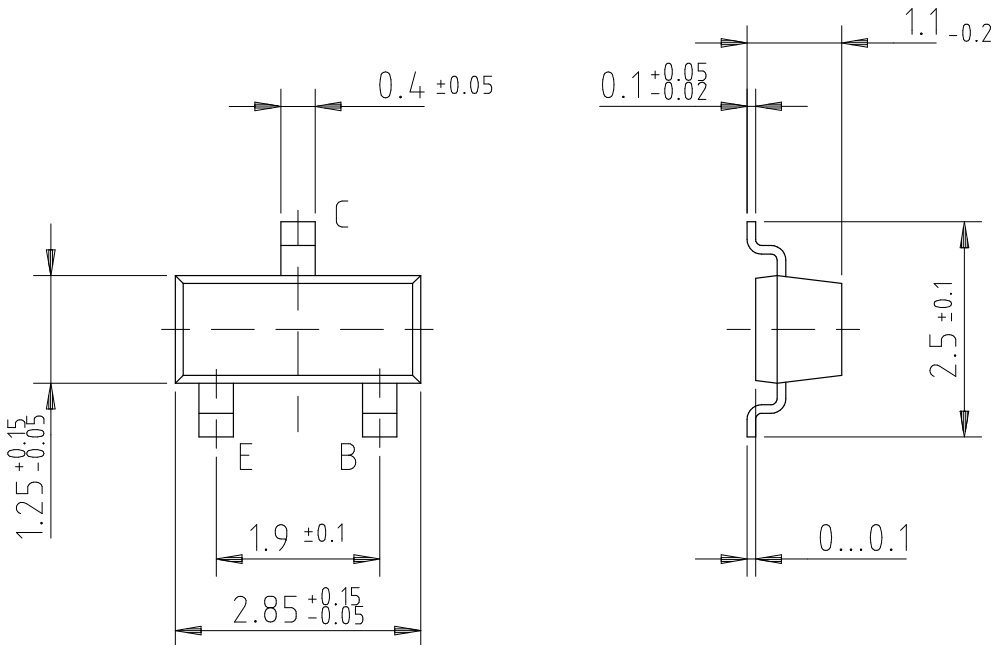


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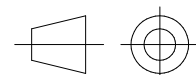


technical drawings  
according to DIN  
specifications

## Dimensions of BFR93R in mm



95 11347



technical drawings  
according to DIN  
specifications

## **Ozone Depleting Substances Policy Statement**

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

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